

L Number	Hits	Search Text	DB	Time stamp
1	3	365/158,243,163,113,105,96,103,104,175.cc1 and high-resistance same low-resistance same heat	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/17 11:20
6	305	365/\$.cc1s. and (heat\$3 or thermal) near5 cell\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/17 11:55
7	100	365/158,175,113,163,171,189.03,177,105,148, and (heat\$3 or thermal) near5 cell\$3	USPAT85.11. US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/17 11:57
8	26	365/158,175,113,163,171,189.03,177,105,148, and (heat\$3 or thermal) near5 cell\$3 and transistor\$1 and diode	USPAT85.11. US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/17 11:57
9	26	365/158,175,113,163,171,189.03,177,105,148, and (heat\$3 or thermal) near5 cell\$3 and \$8transistor and diode	USPAT85.11. US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/17 11:58
-	101	high-resistance same low-resistance same heat	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/17 11:20
-	4	365/\$.cc1s. and high-resistance same low-resistance same heat	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/04 11:37
-	4	("4177475" "4203123" "4499557" "4531144").PN.	USPAT	2004/09/04 11:33
-	1	high-resistance same low-resistance same heat same switch\$3 same transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/04 11:39
-	10	high-resistance same low-resistance same heat same switch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/04 11:56
-	5	("1758703" "2360299" "3475588" "3624354" "3982092").PN.	USPAT	2004/09/04 11:42
-	333	(heat with rate) same transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/17 11:36
-	3	365/\$.cc1s. and (heat with rate) same transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/04 11:59
-	2	("5119329" "5506748").PN.	USPAT	2004/09/04 11:58
-	73	(heat with rate) same switch\$3 same transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/04 11:59

	637	ovonic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/07 08:36
	1	ovonic same (heat\$3 with rate\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/07 07:37
	40	ovonic same heat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/07 08:09
	15	ovonic same transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/07 08:10
	77	365/\$.ccls. and ovonic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/07 08:36
	60	365/\$.ccls. and ovonic and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/07 10:08
	8	365/\$.ccls. and ovonic and transistor near4 heat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/07 10:17
	32	365/\$.ccls. and ovonic and transistor and heat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/07 10:43
	60	365/\$.ccls. and ovonic and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/07 12:13
	19	365/\$.ccls. and ovonic and (transistor with array\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/07 12:23
	2	("5363329" "5920788").PN.	USPAT	2004/09/07 12:15
	2	365/\$.ccls. and (ovonic with heat\$3) and (transistor with array\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/07 12:24
	19	365/\$.ccls. and (ovonic or phase-changeable) and (transistor with array\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/07 12:25
	8	365/\$.ccls. and (ovonic or phase-changeable) and (transistor with array\$1) and heat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/07 12:26
	12	(ovonic or phase-changeable) and (transistor with array\$1) and heat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/07 12:47

-	6	("5439833" "5640343" "6215140" "6339544" "6552926" "6597031" "2003/0076703").PN.	USPAT	2004/09/07 12:27
-	2	("5363329" "5920788").PN.	USPAT	2004/09/07 12:28
-	3	("3206730" "3488636" "3201764").PN.	USPAT	2004/09/07 12:29
-	2	("5296716" "6087674" "2003/0186481" "2003/0206512").PN.	USPAT	2004/09/07 12:29
-	32	(ovonic or phase-changeable) and (transistor with array\$1)	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/07 12:45
-	7	(ovonic or phase-changeable) and (transistor near4 array\$1) and heat\$3	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/07 13:32
-	50	(ovonic or phase-changeable) and (switch\$3 with transistor)	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/07 13:33
-	9	(ovonic or phase-changeable) and (switch\$3 with transistor with heat\$3)	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/07 13:34
-	4	("6191973" "6625054" "6673691" "6700813").PN.	USPAT	2004/09/07 13:35
-	49158	(heat\$3 or thermal) near5 cell\$3	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 11:37
-	301	365/\$158,243,163.ccls. and (heat\$3 or thermal) near5 cell\$3	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/08 15:42
-	24	365/\$158,243,163.ccls. and (heat\$3 or thermal) near5 cell\$3 with transistor\$1	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/08 15:50
-	26	365/158,243,163.ccls. and (heat\$3 or thermal) near5 cell\$3	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/08 15:52
-	14	365/158,243,163.ccls. and (heat\$3 or thermal) near5 cell\$3 and transistor	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/08 16:09
-	15	365/158,243,163,113.ccls. and (heat\$3 or thermal) near5 cell\$3 and transistor	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/09 13:27
-	10	365/\$.ccls. and (heat\$3 or thermal) near5 drain near5 cell\$1 and transistor\$1	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/08 16:24
-	31	365/\$.ccls. and drain with (heat\$3 or thermal) near5 cell\$1 and transistor\$1	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/08 16:40

-	3	drain near3 (heat\$3 or thermal) near5 cell\$1 and transistor\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2004/09/08 16:49
-	7	("4165642" "4734641" "5309090" "5414370" "5473259" "5886564" "5911897").PN.		2004/09/08 16:42
-	45	drain near5 (heat\$3 or thermal) near5 cell\$1 and transistor\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2004/09/08 16:49
-	35	365/158,243,163,113,105,96,103,104,175.cccls and (heat\$3 or thermal) near5 cell\$3 and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2004/09/09 13:29
-	30	365/158,243,163,113,105,96,103,104,175.cccls and (heat\$3 or thermal) near5 diode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2004/09/09 13:37
-	10	365/158,243,163,113,105,96,103,104,175.cccls and ((heat\$3 or thermal) near diode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2004/09/15 09:35
-	1	365/158,243,163,113,105,96,103,104,175.cccls and ((heat\$3 or thermal) near diode and (zener adj diode\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2004/09/09 13:50
-	1	365/\$.cccls. and ((heat\$3 or thermal) near diode and (zener adj diode\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2004/09/09 13:51
-	118	((heat\$3 or thermal) near diode and (zener adj diode\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2004/09/09 13:52
-	75	((heat\$3 or thermal) near diode and (zener adj diode\$1)) and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2004/09/09 13:52
-	1	365/158,243,163,113,105,96,103,104,175.cccls and ((heat\$3 or thermal) near diode and (zener adj diode\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2004/09/09 14:04
-	3	365/158,243,163,113,105,96,103,104,175.cccls and ((heat\$3 or thermal) near5 diode and (zener adj diode\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2004/09/09 14:07
-	4	365/\$.cccls. and ((heat\$3 or thermal) near5 diode and (zener adj diode\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2004/09/09 14:11
-	14	((heat\$3 or thermal) near5 diode and (zener adj diode\$1)) and (thermal adj resistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2004/09/09 14:16

-	9	((heat\$3 or thermal) near5 diode and (zener adj diode\$1)) and (thermal adj resistor) and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/09 14:16
-	1	heat\$3 near4 switch\$3 near4 memory near4 diode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 08:59
-	7	365/\$.ccls. and heat\$3 same switch\$3 same memory same diode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 09:12
-	9	heat\$3 with switch\$3 with memory with diode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 09:13
-	104	heat\$3 same switch\$3 same memory same diode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 09:15
-	2	("4649333" "6002239").PN.	USPAT	2004/09/15 09:23
-	30	365/158,243,163,113,105,96,103,104,175.cccls and ((heat\$3 or thermal) near5 diode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 09:36
-	1	365/158,243,163,113,105,96,103,104,175.cccls and ((heat\$3 or thermal) near5 switch\$3 near5 memory near5 diode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 09:37
-	3	365/158,243,163,113,105,96,103,104,175.cccls and ((heat\$3 or thermal) same switch\$3 same memory same diode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/17 11:31
-	4	("3612758" "3681754" "5592409" "5889694").PN.	USPAT	2004/09/15 09:42
-	9	365/\$.cccls. and ((heat\$3 or thermal) same switch\$3 same memory same diode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 09:45
-	130	((heat\$3 or thermal) same switch\$3 same memory same diode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 09:45